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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	40-WFQFN Exposed Pad
Supplier Device Package	40-HWQFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101eadna-u0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(1/12)

Pin	Package	Data	Fields of	Ordering Part Number
count	. askago	flash	Application Note	S. Golffig Fatt Harrison
20 pins	20-pin plastic LSSOP	Mounted	A	R5F1006AASP#V0, R5F1006CASP#V0, R5F1006DASP#V0,
20 piris	(7.62 mm (300), 0.65	Mounted	A	R5F1006AASF#V0, R5F1006CASF#V0, R5F1006DASF#V0,
	mm pitch)			R5F1006AASP#X0, R5F1006CASP#X0, R5F1006DASP#X0,
	min pitch)			R5F1006EASP#X0
			D	R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0,
				R5F1006EDSP#V0
				R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0,
				R5F1006EDSP#X0
			G	R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0,
				R5F1006EGSP#V0
				R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0,
				R5F1006EGSP#X0
		Not	Α	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0,
		mounted		R5F1016EASP#V0
				R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0,
				R5F1016EASP#X0
			D	R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0,
				R5F1016EDSP#V0
				R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0,
				R5F1016EDSP#X0
24 pins	24-pin plastic	Mounted	Α	R5F1007AANA#U0, R5F1007CANA#U0, R5F1007DANA#U0,
	HWQFN (4 × 4mm,			R5F1007EANA#U0
	0.5 mm pitch)			R5F1007AANA#W0, R5F1007CANA#W0, R5F1007DANA#W0,
				R5F1007EANA#W0
			D	R5F1007ADNA#U0, R5F1007CDNA#U0, R5F1007DDNA#U0,
				R5F1007EDNA#U0
				R5F1007ADNA#W0, R5F1007CDNA#W0, R5F1007DDNA#W0,
				R5F1007EDNA#W0
			G	R5F1007AGNA#U0, R5F1007CGNA#U0, R5F1007DGNA#U0,
				R5F1007EGNA#U0
				R5F1007AGNA#W0, R5F1007CGNA#W0, R5F1007DGNA#W0,
				R5F1007EGNA#W0
		Not	Α	R5F1017AANA#U0, R5F1017CANA#U0, R5F1017DANA#U0,
		mounted		R5F1017EANA#U0
				R5F1017AANA#W0, R5F1017CANA#W0, R5F1017DANA#W0,
				R5F1017EANA#W0
			D	R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0,
				R5F1017EDNA#U0
				R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0,
				R5F1017EDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(5/12)

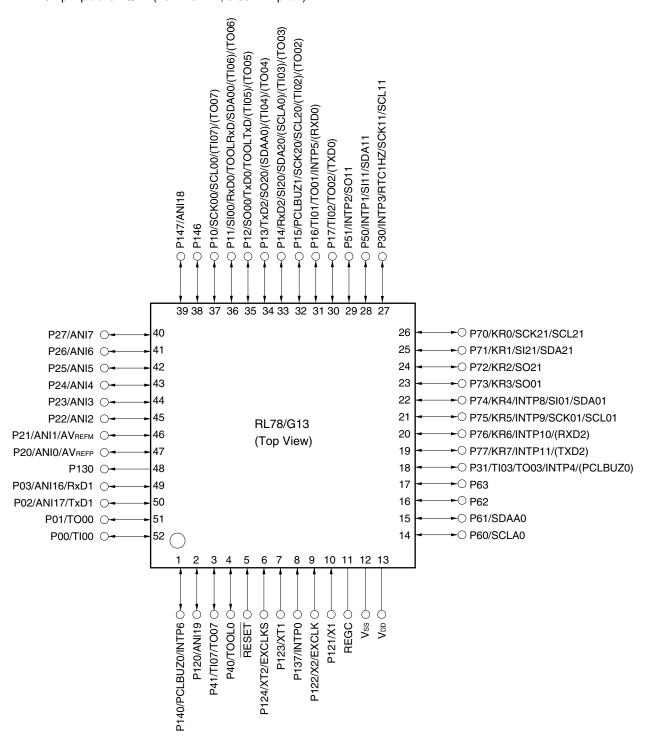
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
48 pins	48-pin plastic	Mounted	Α	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0,
	LFQFP ($7 \times 7 \text{ mm}$,			R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0,
	0.5 mm pitch)			R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0,
				R5F100GLAFB#V0
				R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0,
				R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0,
				R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0,
				R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0,
				R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0,
				R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0,
				R5F100GLDFB#V0
				R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0,
				R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0,
				R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0,
				R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0,
				R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0,
				R5F100GHGFB#V0, R5F100GJGFB#V0
				R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0,
				R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0,
				R5F100GHGFB#X0, R5F100GJGFB#X0
		Not	Α	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0,
		mounted		R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0,
				R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0,
				R5F101GLAFB#V0
				R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0,
				R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0,
				R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0,
				R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0,
				R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0,
				R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0,
				R5F101GLDFB#V0
				R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0,
				R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0,
1				R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0,
				R5F101GLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.10 52-pin products

• 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

3. When setting to PIOR = 1

(2/2)

										(2)	(2)
Ite	m	40-	pin	44	pin	48-	pin	52	-pin	64	-pin
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	2	2		2		2		2		2
·	·	 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation) 									
8/10-bit resolution	A/D converter	9 channe	ls	10 chanr	nels	10 chanr	nels	12 chanr	nels	12 chanr	nels
Serial interface	I ² C bus	• CSI: 1 • CSI: 2 [48-pin, 5 • CSI: 2 • CSI: 1 • CSI: 2 [64-pin pr • CSI: 2 • CSI: 2 • CSI: 2 • CSI: 2	channel/s channels/ channels/ 2-pin proc channels/ channels/ coducts] channels/ channels/	implified I ² implified I ² (simplified ducts] (simplified I ² (simplified I ² (simplified I ² (simplified (simplified I ² (simplified I	1 ² C: 2 char C: 1 chanr 1 ² C: 2 char 1 ² C: 2 char 1 ² C: 2 char 1 ² C: 2 char	nel/UART: nnels/UAR nnels/UART: nnels/UAR nnels/UAR nnels/UAR nnels/UAR	1 channel T (UART: T: 1 channel T (UART: T: 1 channel T: 1 channel T: 1 channel	l supporting nel l supporting nel	ı LIN-bus): ı LIN-bus):	: 1 channe : 1 channe : 1 channe	l I
accumulator DMA controller	uei/munpiy-	32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 2 channels									
Vectored	Internal		7	1	27		27		27		27
interrupt sources	External		7		7		10		12		 13
Key interrupt	1	4	1		4		6		8		8
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access 									
Power-on-reset ci	rcuit	Power- Power-		1.51 V et: 1.50 V	` ,						
Voltage detector		Rising Falling	-		to 4.06 V (to 3.98 V (
On-chip debug fur	nction	Provided									
Power supply volt	age	V _{DD} = 2.4	to 5.5 V ($T_A = -40 \text{ to}$ $T_A = -40 \text{ to}$	+105°C)						
Operating ambien	t temperature				ier applica rial applica		ndustrial a	pplications	s)		

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

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2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit			
Supply	I _{DD1}	Operating	HS (high-	fin = 32 MHz ^{Note 3}	Basic	$V_{DD} = 5.0 \text{ V}$		2.1		mA			
current Note 1		mode	speed main) mode Note 5		operation	$V_{DD} = 3.0 \text{ V}$		2.1		mA			
			mode		Normal	$V_{DD} = 5.0 \text{ V}$		4.6	7.0	mA			
					operation	V _{DD} = 3.0 V		4.6	7.0	mA			
				fin = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.7	5.5	mA			
					operation	V _{DD} = 3.0 V		3.7	5.5	mA			
				fin = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2.7	4.0	mA			
					operation	V _{DD} = 3.0 V		2.7	4.0	mA			
			LS (low-	fin = 8 MHz Note 3	Normal	$V_{DD} = 3.0 \text{ V}$		1.2	1.8	mA			
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.2	1.8	mA			
			LV (low-	fin = 4 MHz Note 3	Normal	$V_{DD} = 3.0 \text{ V}$		1.2	1.7	mA			
			voltage main) mode		operation	V _{DD} = 2.0 V		1.2	1.7	mA			
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.6	mA			
			speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.2	4.8	mA			
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.6	mA			
				V _{DD} = 3.0 V	operation	Resonator connection		3.2	4.8	mA			
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.7	mA			
							V _{DD} = 5.0 V	operation	Resonator connection		1.9	2.7	mA
						$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.7	mA	
				V _{DD} = 3.0 V	operation	Resonator connection		1.9	2.7	mA			
			LS (low-	$f_{MX} = 8 MHz^{Note 2},$	Normal	Square wave input		1.1	1.7	mA			
			speed main) mode Note 5	V _{DD} = 3.0 V	operation	Resonator connection		1.1	1.7	mA			
				$f_{MX} = 8 MHz^{Note 2},$	Normal	Square wave input		1.1	1.7	mA			
				V _{DD} = 2.0 V	operation	Resonator connection		1.1	1.7	mA			
			Subsystem	fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μА			
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Resonator connection		4.2	5.0	μА			
				fsuB = 32.768 kHz	Normal	Square wave input		4.1	4.9	μA			
				Note 4 TA = +25°C	operation	Resonator connection		4.2	5.0	μА			
				fsuB = 32.768 kHz	Normal	Square wave input		4.2	5.5	μΑ			
				Note 4 $T_A = +50^{\circ}C$	operation	Resonator connection		4.3	5.6	μА			
				fsuв = 32.768 kHz	Normal	Square wave input		4.3	6.3	μΑ			
				Note 4 TA = +70°C	operation	Resonator connection		4.4	6.4	μА			
				fsuB = 32.768 kHz	Normal	Square wave input		4.6	7.7	μА			
				Note 4 $T_A = +85^{\circ}C$	operation	Resonator connection		4.7	7.8	μА			

(Notes and Remarks are listed on the next page.)



(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fin = 32 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		2.3		mA
Current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		2.3		mA
			modo		Nomal	V _{DD} = 5.0 V		5.2	8.5	mA
					operation	V _{DD} = 3.0 V		5.2	8.5	mA
				fin = 24 MHz Note 3	Nomal	V _{DD} = 5.0 V		4.1	6.6	mA
					operation	V _{DD} = 3.0 V		4.1	6.6	mA
				fin = 16 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.0	4.7	mA
					operation	V _{DD} = 3.0 V		3.0	4.7	mA
			LS (low-	f _{IH} = 8 MHz ^{Note 3}	Normal	V _{DD} = 3.0 V		1.3	2.1	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.3	2.1	mA
			LV (low-	fin = 4 MHz Note 3	Nomal	V _{DD} = 3.0 V		1.3	1.8	mA
			voltage main) mode		operation	V _{DD} = 2.0 V		1.3	1.8	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.4	5.5	mA
			speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.6	5.7	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.4	5.5	mA
			V _{DD} = 3.0 V	operation	Resonator connection		3.6	5.7	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.1	3.2	mA
				V _{DD} = 5.0 V	operation	Resonator connection		2.1	3.2	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Nomal	Square wave input		2.1	3.2	mA
				V _{DD} = 3.0 V	operation	Resonator connection		2.1	3.2	mA
			LS (low-	$f_{MX} = 8 MHz^{Note 2},$	Normal	Square wave input		1.2	2.0	mA
			speed main) mode Note 5	V _{DD} = 3.0 V	operation	Resonator connection		1.2	2.0	mA
			modo	$f_{MX} = 8 MHz^{Note 2}$	Normal	Square wave input		1.2	2.0	mA
				V _{DD} = 2.0 V	operation	Resonator connection		1.2	2.0	mA
			Subsystem	fsub = 32.768 kHz	Nomal	Square wave input		4.8	5.9	μA
			clock operation	T _A = -40°C	operation	Resonator connection		4.9	6.0	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		4.9	5.9	μΑ
				T _A = +25°C	operation	Resonator connection		5.0	6.0	μΑ
				fsuB = 32.768 kHz	Normal	Square wave input		5.0	7.6	μΑ
				Note 4	operation	Resonator connection		5.1	7.7	μΑ
				T _A = +50°C	Nies 1	0		5 0	0.0	
				fsub = 32.768 kHz	Normal operation	Square wave input		5.2	9.3	μA
				T _A = +70°C	Sporador1	Resonator connection		5.3	9.4	μΑ
				fsub = 32.768 kHz	Normal operation	Square wave input		5.7	13.3	μA
				T _A = +85°C	υρειαιιστ	Resonator connection		5.8	13.4	μA

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 16 \text{ MHz}$ LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 8 \text{ MHz}$

LS (low-speed main) mode: 1.8 V \leq V_{DD} \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq V_{DD} \leq 5.5 V@1 MHz to 4 MHz

- **8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

2.4 AC Characteristics

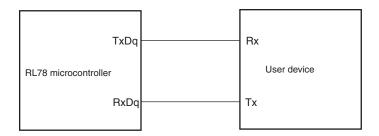
(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Items	Symbol		Conditions	·	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main	HS (high-	$2.7V\!\leq\!V_{DD}\!\leq\!5.5V$	0.03125		1	μS
instruction execution time)		system clock (fmain)	speed main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		operation	LS (low-speed main) mode	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.125		1	μS
			LV (low- voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μS
		Subsystem of	clock (fsuв)	1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μS
		operation						
		In the self	HS (high-	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
		programming mode	speed main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
			LS (low-speed main) mode	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.125		1	μS
			LV (low- voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μS
External system clock	fex	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ V _{DD} <			1.0		16.0	MHz
		1.8 V ≤ V _{DD} <	< 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} <			1.0		4.0	MHz
	fexs				32		35	kHz
External system clock input	texh, texl	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		24			ns
high-level width, low-level width		$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$			30			ns
		1.8 V ≤ V _{DD} <	< 2.4 V		60			ns
		1.6 V ≤ V _{DD} <	< 1.8 V		120			ns
	texhs, texhs				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	fто	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			1.8 V	≤ EV _{DD0} < 2.7 V			4	MHz
			1.6 V	≤ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spec	ed 1.8 V	$\leq EV_{DD0} \leq 5.5 V$			4	MHz
		main) mode	1.6 V	≤ EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode	age 1.6 V	\leq EV _{DD0} \leq 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	$\leq EV_{DD0} \leq 5.5 V$			16	MHz
frequency		main) mode		≤ EV _{DD0} < 4.0 V			8	MHz
				\leq EV _{DD0} $<$ 2.7 V			4	MHz
				≤ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spec		\leq EV _{DD0} \leq 5.5 V			4	MHz
		main) mode	_	≤ EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode		\leq EV _{DD0} \leq 5.5 V \leq EV _{DD0} $<$ 1.8 V			2	MHz MHz
Interrupt input high-level width,	tinth,	INTP0		≤ V _{DD} ≤ 5.5 V	1		=	μS
low-level width	tintl	INTP1 to INT		≤ EV _{DD0} ≤ 5.5 V	1			μS
Karrintanının tianın tarınlarınl	tkr	KR0 to KR7		≤ EV _{DD0} ≤ 5.5 V	250			ns
Key interrupt input low-level					1		1	
Key interrupt input low-level width			1.6 V	≤ EV _{DD0} < 1.8 V	1			μS

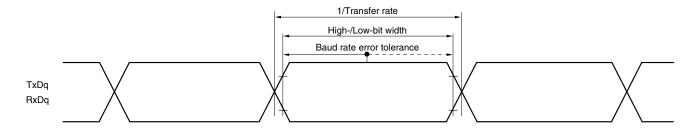
(Note and Remark are listed on the next page.)



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13))

220

220

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ Parameter Symbo Conditions HS (high-speed LS (low-speed main) LV (low-voltage main) Unit main) Mode ı Mode Mode MIN. MIN. MAX. MIN. MAX. MAX. Slp setup time tsik2 $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$ $1/f_{MCK}+2$ 1/fmck+30 1/fmck+30 ns (to SCKp↑) Note 1 n $1.8~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+3 1/fмск+30 1/fмcк+30 ns 0 $1.7~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+4 $1/f_{MCK}+40$ $1/f_{MCK}+40$ ns 0 1/fмск+40 1/fмск+40 $1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$ ns Slp hold time tks12 $1.8~V \leq EV_{DD0} \leq 5.5~V$ 1/fмcк+3 1/fмcк+31 1/fмcк+31 ns (from SCKp↑) 1 $1.7~V \leq EV_{DD0} \leq 5.5~V$ 1/fмcк+ 1/fмск+ 1/fмcк+ ns 250 250 250 $1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$ 1/fmck+ 1/fмcк+ ns 250 250 2/f_{MCK+} 2/f_{MCK+} Delay time tks02 C = 30 $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ ns pF Note 4 from SCKp↓ to 44 110 110 SOp output Note $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ 2/fмcк+ 2/fмск+ ns 110 75 110 2/fмск+ $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fмск+ 2/fмск+ ns 110 110 110 $1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ 2/fmck+ 2/fмск+ ns 220 220 220 $1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fмск+ 2/fмск+ ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00 to 03, 10 to 13))

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

(TA = -40 to +85°C, 2.7 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol		Conditions	HS (hig		LS (low main)	-speed	LV (low- main)	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 20 \; pF, \; R_b = 1.4 \\ &k\Omega \end{aligned} $	200		1150		1150		ns
			$\begin{split} & 2.7 \; \text{V} \leq \text{EV}_{\text{DD0}} < 4.0 \; \text{V}, \\ & 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ & C_{\text{b}} = 20 \; \text{pF}, \; R_{\text{b}} = 2.7 \\ & \text{k}\Omega \end{split}$	300		1150		1150		ns
SCKp high-level width	tкнı	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	tксү1/2 — 50		tксу1/2 — 50		tксү1/2 — 50		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ pF, F}$	2.7 V,	tксу1/2 — 120		tксу1/2 — 120		tксу1/2 — 120		ns
SCKp low-level width	tĸL1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 6$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	tксү1/2 — 7		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 3$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	tксу ₁ /2 – 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) Note 1	tsıĸı	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	58		479		479		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2$ $C_{b} = 20 \text{ pF, F}$	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4$ $C_{b} = 20 \text{ pF, F}$	4.0 V,	10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2$ $C_{b} = 20 \text{ pF}, \text{ F}$	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ C}$ $C_{b} = 20 \text{ pF, F}$	o ≤ 5.5 V, 4.0 V,		60		60		60	ns
		$2.7 \text{ V} \le \text{EV}_{DD}$ $2.3 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 20 \text{ pF, F}$	o < 4.0 V, 2.7 V,		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	` `	h-speed Mode	`	/-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸı	$\begin{array}{l} 4.0~V \leq EV_{DD0} \leq 5.5~V, \\ 2.7~V \leq V_b \leq 4.0~V, \end{array}$	81		479		479		ns
		$C_b = 30$ pF, $R_b = 1.4$ k Ω							
			177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	479		479		479		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
SIp hold time (from SCKp↑) Note 1	t KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
Delay time from SCKp↓ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		483		483		483	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							

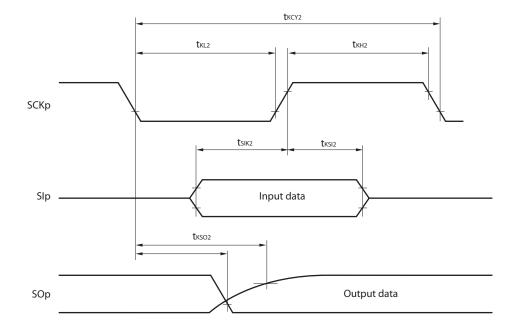
Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with $EV_{DD0} \ge V_b$.

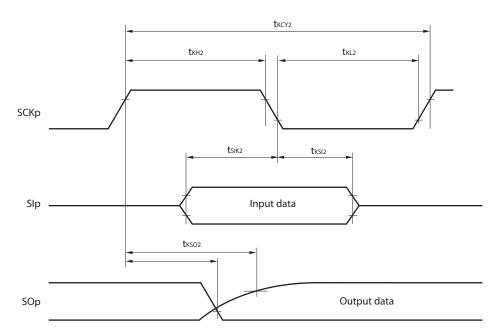
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (–) = AVREFM
ANI0 to ANI14	Refer to 2.6.1 (1) .	Refer to 2.6.1 (3) .	Refer to 2.6.1 (4) .
ANI16 to ANI26	Refer to 2.6.1 (2) .		
Internal reference voltage	Refer to 2.6.1 (1) .		_
Temperature sensor output			
voltage			

(1) When reference voltage (+)= AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±3.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2 to	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI14	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Full-scale error Notes 1, 2	E _{FS}	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±2.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±1.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±2.0	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS		V _{BGR} Note 5		V	
		Temperature sensor outp (2.4 V \leq VDD \leq 5.5 V, HS	•	\	/TMPS25 Note	5	V

(Notes are listed on the next page.)



LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit	
Interrupt and reset	V _{LVDA0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 0, 0	, falling reset voltage	1.60	1.63	1.66	V	
mode	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V	
				Falling interrupt voltage	1.70	1.73	1.77	V	
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	٧	
				Falling interrupt voltage	1.80	1.84	1.87	V	
	VLVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V	
				Falling interrupt voltage	2.80	2.86	2.91	٧	
	V _{LVDB0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 0, 1	, falling reset voltage	1.80	1.84	1.87	V	
	V _{LVDB1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	>	
				Falling interrupt voltage	1.90	1.94	1.98	٧	
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	٧	
				Falling interrupt voltage	2.00	2.04	2.08	V	
	V _{LVDB3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V	
			Falling interrupt voltage	3.00	3.06	3.12	V		
	V _{LVDC0}	V _{POC2} ,	c2, VPOC1, VPOC0 = 0, 1, 0, falling reset voltage			2.45	2.50	٧	
	VLVDC1			LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V	
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	>	
				Falling interrupt voltage	2.60	2.65	2.70	V	
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	٧	
				Falling interrupt voltage	3.60	3.67	3.74	V	
	V _{LVDD0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 1, 1	, falling reset voltage	2.70	2.75	2.81	V	
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V	
				Falling interrupt voltage	2.80	2.86	2.91	V	
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V	
				Falling interrupt voltage	2.90	2.96	3.02	V	
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V	
				Falling interrupt voltage	3.90	3.98	4.06	V	



Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	٧
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and $-0.3 \text{ to V}_{DD} +0.3^{\text{Note 1}}$	V
Input voltage	VII	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV _{DD0} +0.3	V
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	and -0.3 to V _{DD} +0.3 ^{Note 2}	
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V ₀₁	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV _{DD0} +0.3	٧
		P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	and –0.3 to V _{DD} +0.3 ^{Note 2}	
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	٧
Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V
	V _{Al2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - 2. $AV_{REF}(+)$: + side reference voltage of the A/D converter.
 - 3. Vss : Reference voltage



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	500		ns
SCKp high-/low-level width	t кн1,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tkcy1/2 - 24		ns
	l ⊢	$2.7~V \leq EV_{DD0} \leq 5.5~V$		tkcy1/2 - 36		ns
		2.4 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsıĸı	$4.0~V \leq EV_{DD0} \leq 5.5~V$		66		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$		66		ns
		2.4 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	113		ns
SIp hold time (from SCKp↑) Note 2	t KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	o 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3).
 - g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 - n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0$ $V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$	600		ns
			$2.7~V \leq EV_{DD0} < 4.0~V,~2.3~V \leq V_b \leq 2.7$ $V,$ $C_b = 30~pF,~R_b = 2.7~k\Omega$	1000		ns
			$2.4~V \leq EV_{DD0} < 3.3~V,~1.6~V \leq V_b \leq 2.0$ $V,$ $C_b = 30~pF,~R_b = 5.5~k\Omega$	2300		ns
SCKp high-level width	tкнı		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$			ns
		$2.7~V \leq EV_{DD0} < 4.0~V,~2.3~V \leq V_b \leq 2.7~V,$ $C_b = 30~pF,~R_b = 2.7~k\Omega$		tkcy1/2 - 340		ns
			$V \le EV_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le V_b \le 2.0 \text{ V},$ = 30 pF, $R_b = 5.5 \text{ k}\Omega$			ns
SCKp low-level width	t _{KL1}	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$		tkcy1/2 - 24		ns
		$2.7~V \leq \text{EV}_{\text{DDO}} < 4.0~V,~2.3~V \leq V_{\text{b}} \leq 2.7~V,$ $C_{\text{b}} = 30~\text{pF},~R_{\text{b}} = 2.7~\text{k}\Omega$		tkcy1/2 - 36		ns
		$2.4~V \leq EV_{DD0} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V,$ $C_b = 30~pF,~R_b = 5.5~k\Omega$		tkcy1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (Vpd tolerance (for the 20- to 52-pin products)/EVpd tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

4.8 44-pin Products

R5F100FAAFP, R5F100FCAFP, R5F100FDAFP, R5F100FEAFP, R5F100FFAFP, R5F100FGAFP,

R5F100FHAFP, R5F100FJAFP, R5F100FKAFP, R5F100FLAFP

R5F101FAAFP, R5F101FCAFP, R5F101FDAFP, R5F101FEAFP, R5F101FFAFP, R5F101FGAFP,

R5F101FHAFP, R5F101FJAFP, R5F101FKAFP, R5F101FLAFP

R5F100FADFP, R5F100FCDFP, R5F100FDDFP, R5F100FEDFP, R5F100FFDFP, R5F100FGDFP,

R5F100FHDFP, R5F100FJDFP, R5F100FKDFP, R5F100FLDFP

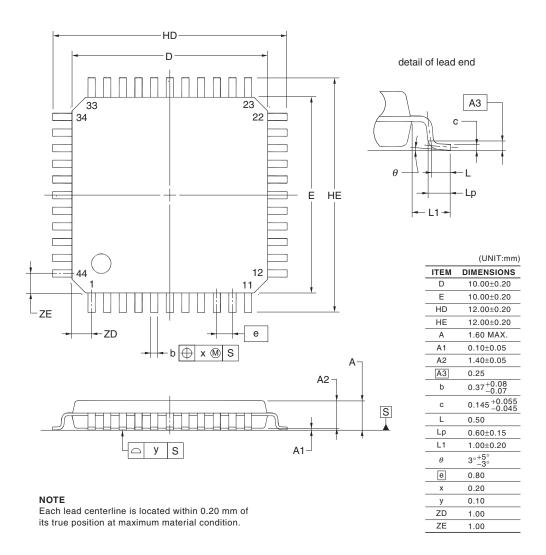
R5F101FADFP, R5F101FCDFP, R5F101FDDFP, R5F101FEDFP, R5F101FFDFP, R5F101FGDFP,

R5F101FHDFP, R5F101FJDFP, R5F101FKDFP, R5F101FLDFP

R5F100FAGFP, R5F100FCGFP, R5F100FDGFP, R5F100FEGFP, R5F100FFGFP, R5F100FGGFP,

R5F100FHGFP, R5F100FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



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